

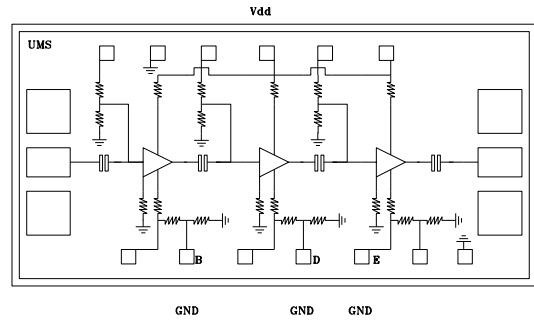
17-24GHz Low Noise Amplifier GaAs Monolithic Microwave IC

Description

The CHA2090-99F is a three-stage self-biased wide band monolithic low noise amplifier.

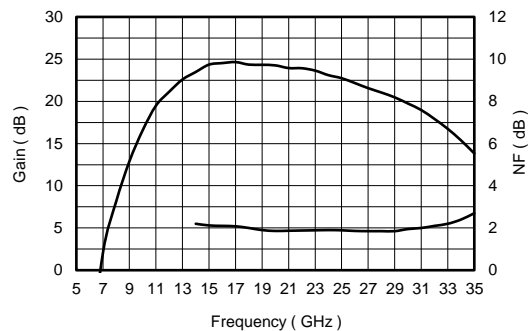
The circuit is manufactured with a standard 0.25µm gate length pHEMT process, via holes through the substrate, air bridges and electron beam gate lithography.

It is supplied in chip form.



Main Features

- Broadband performance 17-24GHz
- 2.0dB noise figure
- 23dB gain, ± 1dB gain flatness
- Low DC power consumption, 55mA
- Chip size: 2,17 x 1,27 x 0.1mm



On wafer typical measurement

Main Characteristics

Tamb = +25°C, Vd=4.5V, Pads B,D,E=GND

Symbol	Parameter	Min	Typ	Max	Unit
Fop	Operating frequency range	17		24	GHz
NF	Noise figure		2.0	3.0	dB
G	Gain	19	23		dB
VSWRin	Input VSWR			2:1	
VSWRout	Output VSWR			2:1	

ESD Protection : Electrostatic discharge sensitive device. Observe handling precautions !

Main Characteristics

Tamb = +25°C, Vd=4.5V, Pads B, D, E=GND

Symbol	Parameter	Min	Typ	Max	Unit
Fop	Operating frequency range	17		24	GHz
NF	Noise figure (1)		2	3	dB
G	Gain (1)	19	23		dB
Pout	Pout -1dB gain compression		10		dBm
VSWRin	Input VSWR (1)		2.0:1	2.5:1	
VSWRout	Output VSWR (1)		2.0:1	2.5:1	
Vdd	Positive Drain voltage (2)		4.5	5.0	V

(1) These values are representative of on-wafer measurements that are made without bonding wires at the RF ports. When the chip is attached with typical 0.15nH input and output bonding wires, the indicated parameter values should be improved.

(2) See chip biasing option page 7/8.

Absolute Maximum Ratings (1)

Tamb = +25°C

Symbol	Parameter	Values	Unit
Vd	Drain bias voltage (3)	5.5	V
Pin	Maximum peak input power overdrive (2)	+15	dBm
Top	Operating temperature range	-40 to +85	°C
Tstg	Storage temperature range	-55 to +150	°C

(1) Operation of this device above anyone of these parameters may cause permanent damage.

(2) Duration < 1s.

(3) See chip biasing option page 7/8.

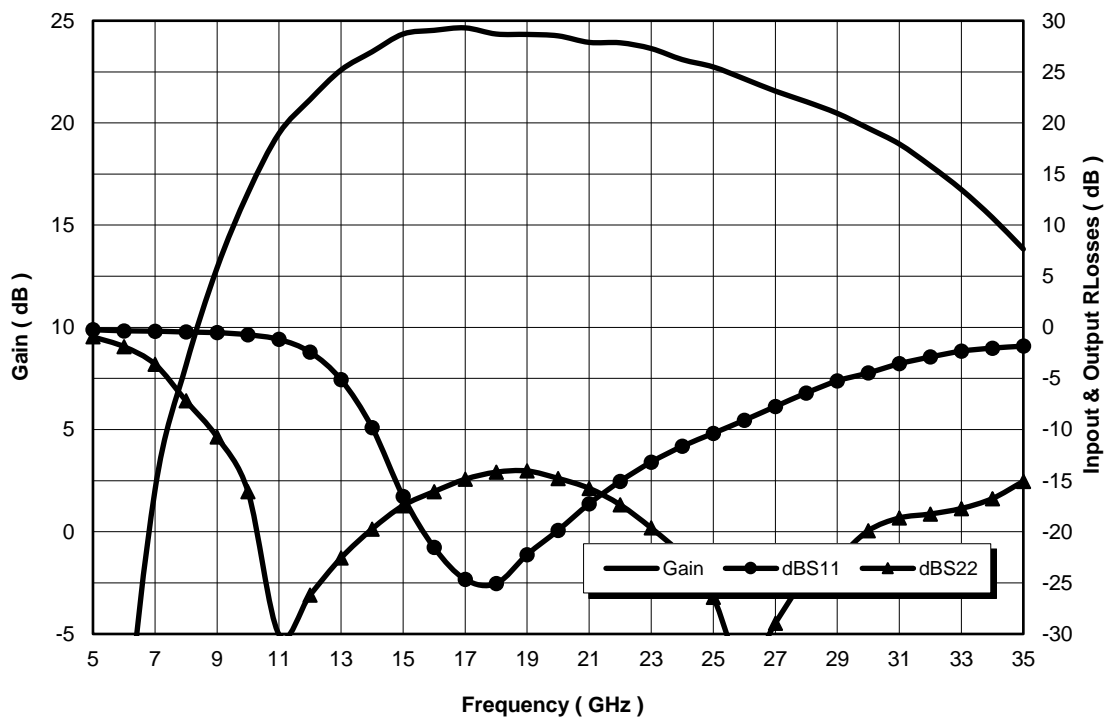
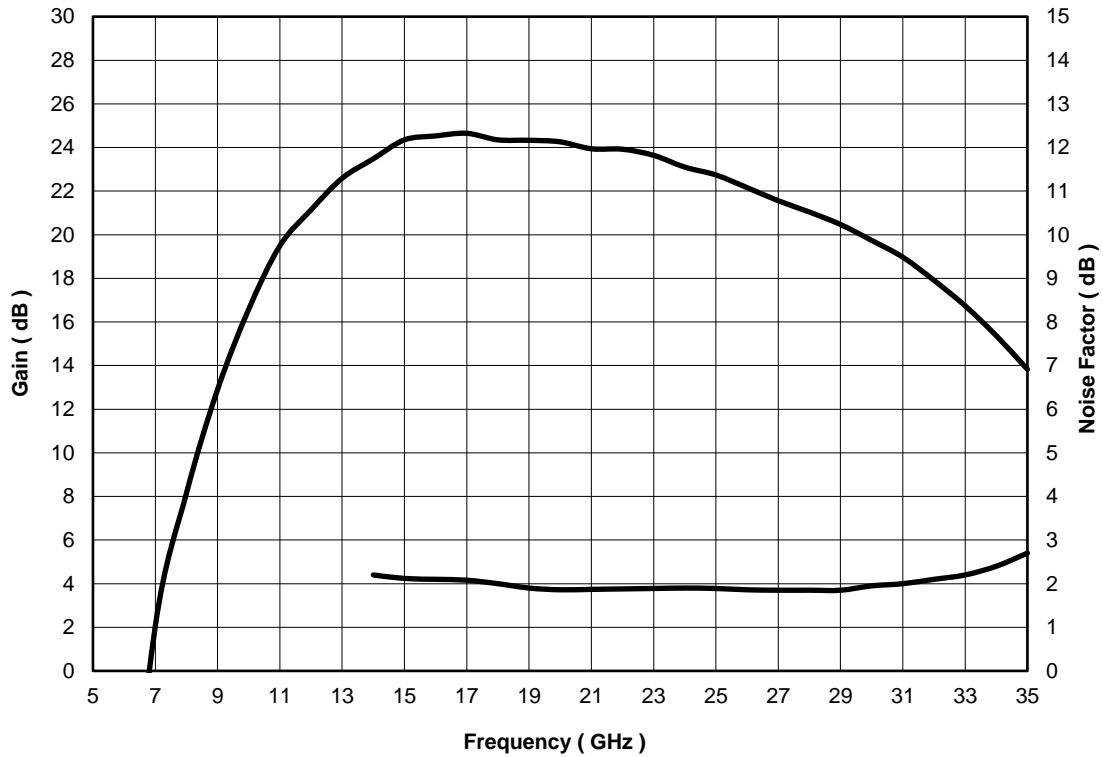
Typical Result**Chip Typical Response (On wafer Sij) :**

Tamb = +25°C VD = 4.5V ID = 55mA

Frequency	MS11 <i>mod</i>	PS11 <i>pha</i>	MS12 <i>mod</i>	PS12 <i>pha</i>	MS21 <i>mod</i>	PS21 <i>pha</i>	MS22 <i>mod</i>	PS22 <i>pha</i>
GHz	dB	deg	dB	deg	dB	deg	dB	deg
1.000	-0.53	-20.8	-89.62	-92.0	-41.76	-148.5	-0.72	-23.8
2.000	-0.06	-39.0	-97.43	26.6	-48.17	170.5	-0.30	-50.3
3.000	-0.10	-58.5	-87.21	-23.0	-52.46	74.5	-0.33	-75.6
4.000	-0.16	-77.4	-84.87	-135.7	-61.22	154.8	-0.49	-101.9
5.000	-0.23	-96.5	-83.35	120.1	-35.86	-69.1	-0.89	-129.8
6.000	-0.34	-115.2	-66.23	84.2	-12.12	-123.6	-1.77	-159.0
7.000	-0.35	-134.1	-72.40	-58.1	1.34	145.9	-3.35	168.8
8.000	-0.45	-154.1	-73.93	-13.6	7.48	75.4	-6.63	141.1
9.000	-0.52	-175.4	-72.23	-7.1	11.96	18.3	-9.34	119.1
10.000	-0.75	160.3	-66.01	-34.2	15.54	-28.2	-13.97	85.5
11.000	-1.21	132.1	-60.26	-60.3	18.30	-72.2	-22.57	53.2
12.000	-2.33	97.8	-56.60	-94.9	19.92	-116.5	-39.69	-60.4
13.000	-4.60	57.2	-53.53	-135.9	21.36	-163.1	-30.19	-133.1
14.000	-8.86	8.5	-52.43	-173.4	22.49	149.3	-25.30	-127.8
15.000	-16.48	-40.4	-52.50	157.8	23.60	100.6	-21.56	-134.5
16.000	-24.70	-70.2	-52.26	135.4	23.89	62.2	-19.34	-144.1
17.000	-27.75	-80.6	-52.62	108.9	24.01	28.4	-17.60	-158.0
18.000	-23.51	-87.4	-51.36	100.6	23.66	-1.9	-16.51	-172.3
19.000	-21.41	-95.7	-51.27	60.6	23.52	-30.5	-16.34	163.7
20.000	-18.63	-107.0	-54.07	52.8	23.46	-57.8	-17.75	149.6
21.000	-16.77	-115.6	-55.06	30.3	23.11	-84.4	-19.33	131.6
22.000	-14.95	-123.2	-57.35	23.7	23.14	-111.0	-22.26	113.9
23.000	-13.73	-132.0	-59.54	8.0	22.82	-137.3	-25.44	89.1
24.000	-12.59	-138.8	-60.85	32.3	22.36	-162.8	-29.95	43.8
25.000	-11.60	-144.7	-62.07	49.5	22.01	171.8	-28.26	-24.5
26.000	-10.61	-149.8	-54.29	40.2	21.46	147.9	-22.90	-58.9
27.000	-9.34	-154.5	-55.03	23.9	20.91	125.0	-19.22	-84.3
28.000	-7.89	-160.6	-52.05	-11.6	20.49	102.3	-17.12	-102.6
29.000	-6.63	-171.3	-60.41	-22.1	20.06	78.5	-16.20	-114.2
30.000	-5.86	179.9	-56.56	23.2	19.50	55.4	-14.73	-123.1
31.000	-4.83	172.0	-52.73	-13.7	19.03	31.5	-13.72	-137.5
32.000	-3.95	161.7	-54.11	-40.7	18.31	6.9	-13.60	-147.0
33.000	-3.18	151.2	-54.59	-51.2	17.51	-17.5	-13.61	-155.8
34.000	-2.61	140.2	-55.15	-37.9	16.54	-42.3	-14.22	-161.4
35.000	-2.15	129.3	-51.68	-92.2	15.35	-66.8	-14.94	-161.8
36.000	-1.77	117.9	-57.64	-111.2	13.94	-91.0	-15.31	-154.5
37.000	-1.65	106.7	-60.87	-68.5	12.41	-114.4	-13.87	-143.9
38.000	-1.64	95.9	-53.10	-33.4	10.67	-137.5	-11.60	-140.4
39.000	-1.65	85.9	-47.45	-99.7	8.76	-159.6	-9.18	-143.5
40.000	-1.76	75.2	-46.80	-137.0	6.70	178.9	-7.06	-151.0

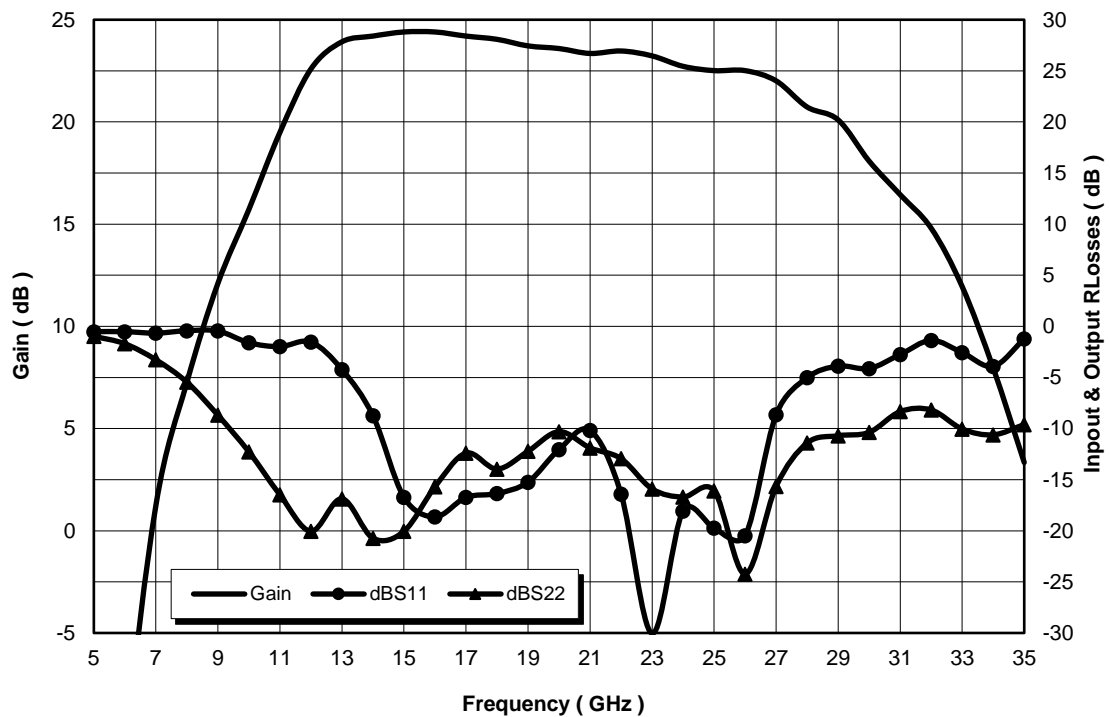
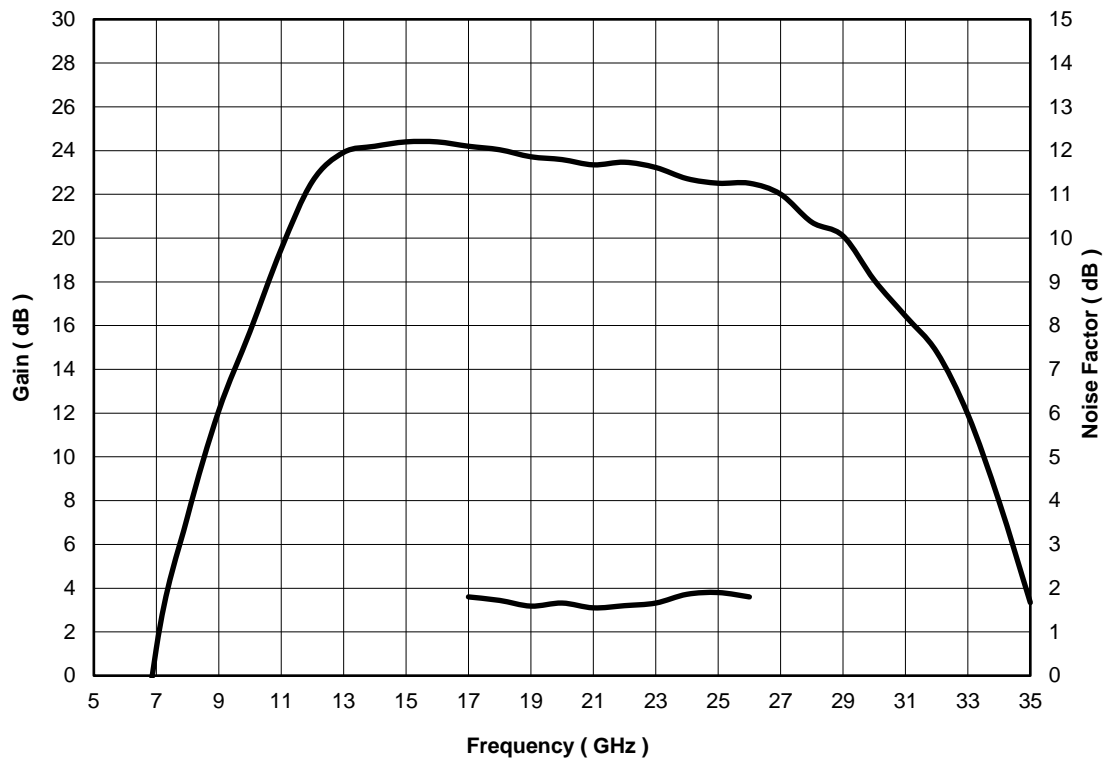
Typical on Wafer Measurements

Bias conditions: $V_d = 4.5V$, $I_d = 55mA$

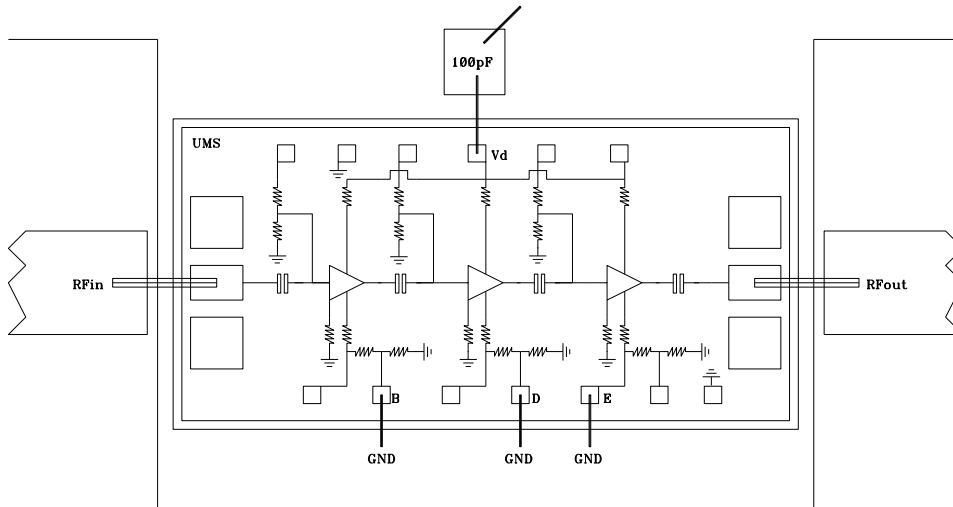


Typical on Test Jig Measurements

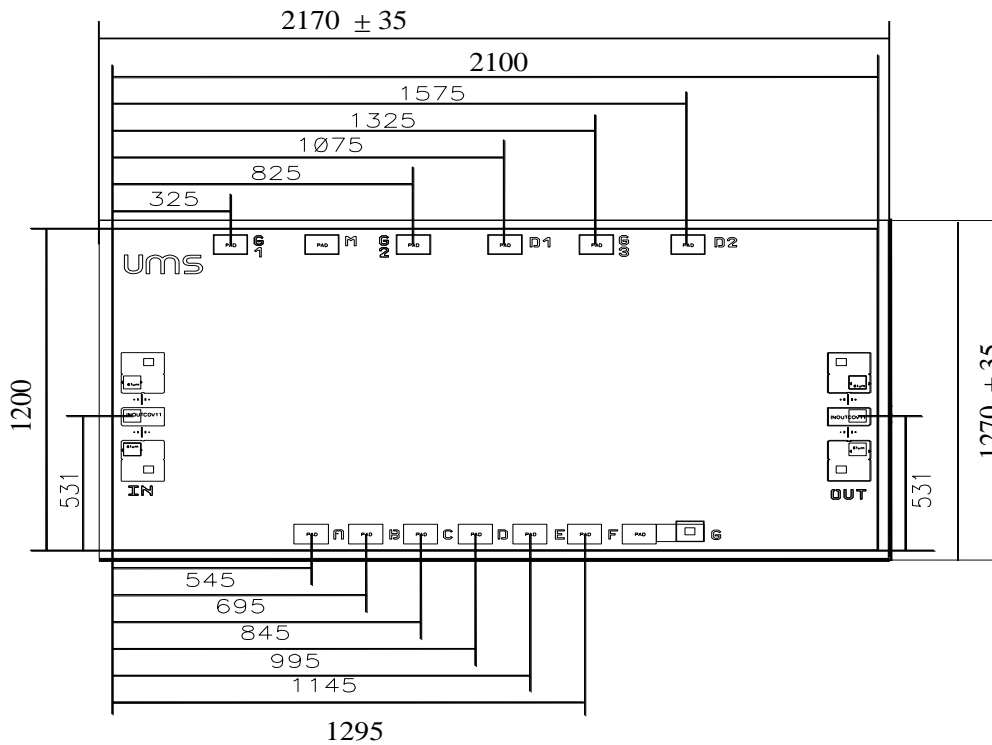
Bias conditions: $V_d = 4.5V$, $I_d = 55mA$



Chip Assembly and Mechanical Data



Note : Supply feed should be capacitively bypassed. 25µm diameter gold wire is to be preferred.



Bonding pad positions.
 (Chip thickness: 100µm. Pad size: 100x80µm²)
 (All dimensions are in micrometers)

Ordering Information

Chip form : CHA2090-99F/00

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